

Monday, June 16, 2003
Poster Session MoP
Marriott Hotel - 5:30 - 7:00pm

MoP-01

External Control of the Direction of Magnetization in Ferromagnetic InMnAs/(Al,Ga)Sb Heterostructures

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MoP-02

Energy Spectrum and Magnetic Properties of New Diluted Magnetic Semiconductors Pb_{1-x}Sn_xTe:Yb

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MoP-03

Electron-Active Cyclotron Resonance in p-type InMnAs in High Magnetic Fields

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MoP-04

Determining Carrier Densities in InMnAs by Cyclotron Resonance

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MoP-05

Experimental and Theoretical Studies of Electronic States and Cyclotron Resonance in InMnAs/InAs Superlattices

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MoP-06

Electronic States and THz Dynamics in Ferromagnetic InGaMnAs

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MoP-07

Magnetic Properties of GaSb/Mn Digital Alloys

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MoP-08

Magnetotransport and Magnetic Properties of InAs/Mn Digital Alloys

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MoP-09

Shake-up Processes in Intersubband Magneto-Photoabsorption of a Two-Dimensional Electron Gas

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MoP-10

Comparison of the Spin-Splitting from Bulk and Structural Asymmetry in Type-II Quantum Wells

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MoP-11

Current Spin-Polarization in Hybrid Wire-Like Structures

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MoP-12

Zero-Field Spin Splitting in Asymmetrical Type-I and Type-II Quantum Well Heterostructures

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MoP-13

Electronic g-Factor in a Gated InAs-Inserted In_{0.53}Ga_{0.47}As/In_{0.52}As_{0.48} As Quantum Well

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MoP-14

Rashba Spin-Splitting in Narrow Gap III-V Semiconductors

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MoP-15

Electron Spin Filtering in All-Semiconductor Tunnel Structures

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MoP-16

Magnetoconductivity Tensor Analysis of Anomalous Transport Effects in Neutron Irradiated HgCdTe Epilayers

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MoP-17

Ballistic Electron Transport in InSb Quantum Wells at High Temperature

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MoP-18

Classical In-Plane Negative Magnetoresistance and Quantum Positive Magnetoresistance in Undoped InSb Thin Films on GaAs (100) Substrates

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MoP-19

Band Structure and Magneto-Transport Properties in Narrow-Gap HgTe/CdTe Superlattice

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MoP-20

New Super-Narrow Gap Semiconductors

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MoP-21

Thermomagnetic Effects under Pressure in PbTe and PbSe

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MoP-22**Spatially - Inhomogeneous Effects at the Interference of Electron Waves in Semiconductor 1D Nanostructures**

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MoP-23**Resonance Scattering on In Impurity in $\text{Pb}_{0.4}\text{Sn}_{0.6}\text{Te}$ Solid Solutions**

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State Technical University, St.-Petersburg, Russia

MoP-24**Correlation of Resonance Scattering and Superconductivity in $\text{Pb}_x\text{Sn}_{1-x}\text{Te}$ Solid Solutions Doped with In**

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TuP-01

Effect of Structural Defects on InSb/Al_xIn_{1-x}Sb Quantum Wells Grown on GaAs (001)

T.D. Mishima, J.C. Keay, N. Goel, M.A. Ball, S.J. Chung, M.B. Johnson, and M.B. Santos
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TuP-02

MOCVD Growth of Undoped and p-Doped GaSb(100)

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TuP-03

Disordering-Induced Effects in p-PbSe Single Crystals

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TuP-04

Transport, Optical and Magneto-Transport Properties of Hetero-Epitaxial InAs_xSb_{1-x}/GaAs and Bulk InAs_xSb_{1-x} ($x \leq 0.06$) Crystals: Experiment and Theoretical Analysis

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TuP-05

High Resolution X-ray Diffraction Analysis of SnTe/Sn_{1-x}Eu_xTe Superlattices Grown on BaF₂(111) Substrates

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TuP-06

Characterization of Intrinsic and Compensated Defect Microstructures in Dilute III-V-N Alloys

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TuP-07

Magnetization and Magnetic Susceptibility on InAs Nano-Rings

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TuP-08

Millisecond Fluorescence in InAs QD's Embedded in AlAs

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TuP-09

Zeeman Effect and Magnetic Anomalies in Narrow-Gap Semiconductor Quantum Dots

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TuP-10

Ultrafast Carrier Dynamics of Resonantly Excited InAs/GaAs Self-Assembled Quantum Dots

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TuP-11

Hybridized Electron States in Self-Assembled Quantum Dots: Kondo Excitons and Auger-like Processes

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TuP-12

Microconstrictions as Generators of Super Narrow Electron Distributions

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TuP-13

Optimization of a Non-Cryogenic Quantum Infrared Detector

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TuP-14

Intersubband Transitions in Coupled InAs/AlSb Quantum Wells

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TuP-15

Design and Fabrication of Infrared Detectors based on Lattice Matched InAs_{0.91}Sb_{0.09} on GaSb

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TuP-16

The Submicrometer Thickness n-InSb/i-GaAs Epilayers for Magnetoresistor Applications at Room Temperatures of Operation

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TuP-17

Up-Conversion of Terahertz Radiation Induced by the Photon Drag Effect

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TuP-18

InAsSb/GaAlSb/InAsSb nBn IR Detector for the 3-5mm

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TuP-19

Many-Body Effects on Intersubband Resonances in Narrow InAs/AlSb Semiconductor Quantum Wells

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TuP-20

Microscopic Modeling of Intersubband Resonances in InAs/AlSb Quantum Wells

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TuP-21

Intersubband Transitions in Narrow InAs/AlSb Quantum Wells

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TuP-22

Optimization of InAs/GaSb Type-II Superlattices for High Performance of Photodetectors

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TuP-23

Resonant-Cavity-Enhanced Photodetectors and LEDs in the Mid-Infrared

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TuP-24

Hot Electrons and Interband Breakdown in a p-type Kane Semiconductor with a Degenerate Hole Distribution

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TuP-25

Calculation of the Auger Recombination Intensity in Kane Semiconductors with Degenerate Carrier Distribution

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